

东莞市华远电子有限公司

DONG GUAN SHI HUA YUAN ELECTRON CO.,LTD.

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TO-92 Plastic-Encapsulate Transistors

2SA950

TRANSISTOR (PNP)

FEATURE

Power dissipation

 P_{CM} : 0.6 W (Tamb=25)

Collector current

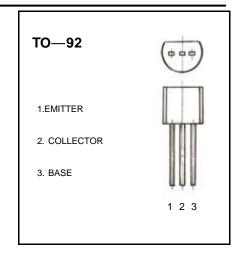
 I_{CM} : -0.8 A

Collector-base voltage

 $V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

Tj, T_{stg} : -55 to +150



ELECTRICAL CHARACTERISTICS (Tamb=25 unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CBO}	Ic= -1mA, I _E =0	-35			V
Collector-emitter breakdown voltage	V(BR) _{CEO}	I _C = -10 mA , I _B =0	-30			V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E = -1Ma, I _C =0	-5			V
Collector cut-off current	Ісво	V _{CB} = -35V, I _E =0			-0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μА
DC autrout sain	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	100		320	
DC current gain	h _{FE(2)}	V _{CE} =-1V, I _C = -700m A	35			
Collector-emitter saturation voltage	ollector-emitter saturation voltage V _{CE(sat)} I _C = -500mA, I _B = -20mA				-0.7	V
Collector Output Capacitance	Cob VCB=-10V,IE=0 f=1MHz			19		pF
Transition frequency	ency f _T V _{CE} =-5V,I _C =-10mA, 12		120		MHz	

CLASSIFICATION OF h_{FE(1)}

Rank	0	Υ	
Range	100-200	160-320	

TO-92 PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.400	4.700	0.173	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.270TYP		0.050TYP		
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ö		1.600		0.063	
$\overline{}$	0.000	0.380	0.000	0.015	